

1     ABSTRACT OF THE DISCLOSURE

2             The invention encompasses a method of removing at least some of  
3     a material from a semiconductor substrate. A feed gas is fed through  
4     an ozone generator to generate ozone. The feed gas comprises at least  
5     99.999% O<sub>2</sub> (by volume). The ozone, or a fragment of the ozone, is  
6     contacted with a material on a semiconductor substrate to remove at  
7     least some of the material from the semiconductor substrate. The  
8     invention also encompasses another method of removing at least some of  
9     a material from a semiconductor substrate. A mixture of ozone and  
10    organic solvent vapors is formed in a reaction chamber. At least some  
11    of the ozone and solvent vapors are contacted with a material on a  
12    semiconductor substrate to remove at least some of the material from  
13    the semiconductor substrate.